

T-29-23

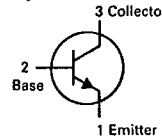
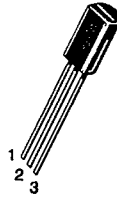
MAXIMUM RATINGS

Rating	Symbol	BDB01A	BDB01B	BDB01C	BDB01D	Unit
Collector-Emitter Voltage	V_{CE0}	45	60	80	100	Vdc
Collector-Base Voltage	V_{CES}	45	60	80	100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0				Vdc
Collector Current - Continuous	I_C	0.5				Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0				Watt mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5 20				Watt mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150				$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	$^\circ\text{C/W}$

BDB01A, B, C, D

CASE 29-03, STYLE 1
TO-92 (TO-226AE)ONE WATT
AMPLIFIER TRANSISTORS

NPN SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Voltage ($I_C = 10\text{ mA}$, $I_B = 0$) BDB01A BDB01B BDB01C BDB01D	$V_{(BR)CE0}$	45 60 80 100		Vdc
Collector Cutoff Current ($V_{CB} = 45\text{ V}$, $I_E = 0$) ($V_{CB} = 60\text{ V}$, $I_E = 0$) ($V_{CB} = 80\text{ V}$, $I_E = 0$) ($V_{CB} = 100\text{ V}$, $I_E = 0$) BDB01A BDB01B BDB01C BDB01D	I_{CBO}		0.1 0.1 0.1 0.1	μAdc
Emitter Cutoff Current ($I_C = 0$, $V_{EB} = 5.0\text{ V}$)	I_{EBO}		100	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 100\text{ mA}$, $V_{CE} = 1\text{ V}$) ($I_C = 500\text{ mA}$, $V_{CE} = 2\text{ V}$)	h_{FE}	40 25	400	
Collector-Emitter Saturation Voltage* ($I_C = 1000\text{ mA}$, $I_B = 100\text{ mA}$)	$V_{CE(sat)}$		0.7	Vdc
Collector-Emitter On Voltage* ($I_C = 1000\text{ mA}$, $V_{CE} = 1\text{ V}$)	$V_{BE(on)}$		1.2	Vdc

DYNAMIC CHARACTERISTICS

Current Gain Bandwidth Product ($I_C = 200\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$)	f_T	50		MHz
Output Capacitance ($V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$)	C_{ob}		30	pF

*Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle 2.0%.

FIGURE 1 - D.C. CURRENT GAIN

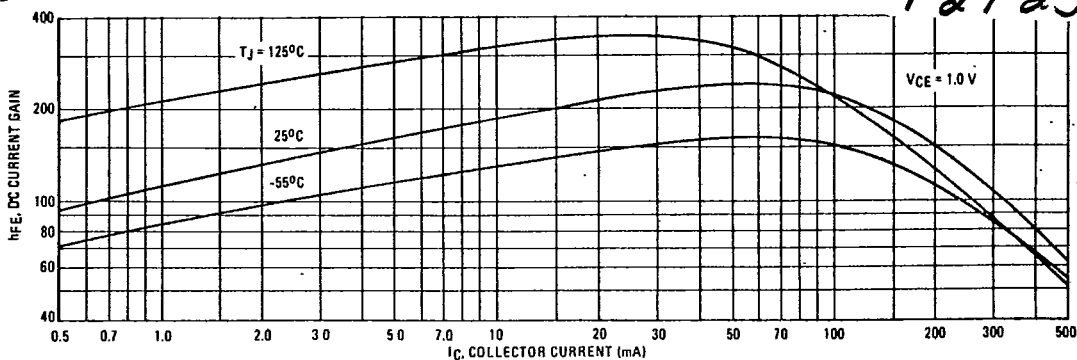


FIGURE 2 - COLLECTOR SATURATION REGION

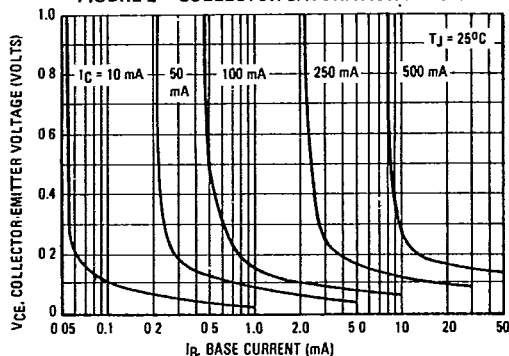


FIGURE 4 - BASE-EMITTER TEMPERATURE COEFFICIENT

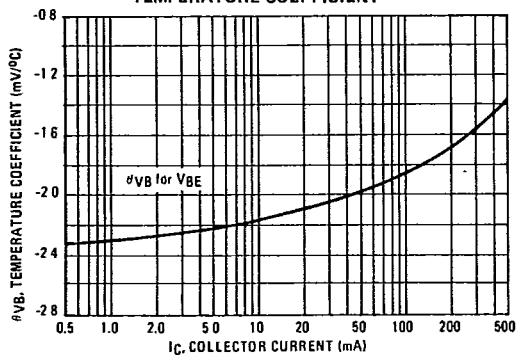


FIGURE 6 - CURRENT GAIN-BANDWIDTH PRODUCT

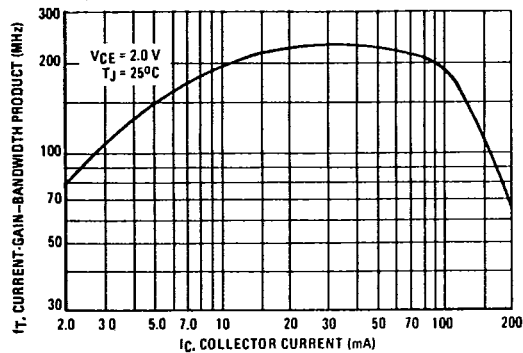


FIGURE 3 - ON VOLTAGES

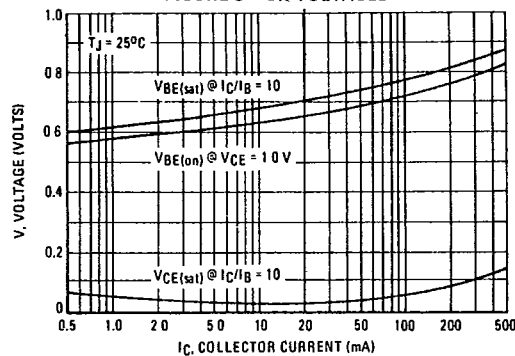


FIGURE 5 - CAPACITANCE

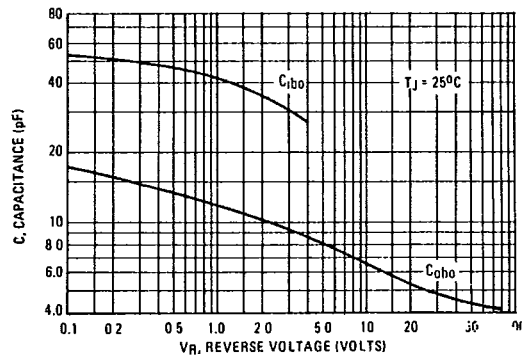


FIGURE 7 - ACTIVE REGION-SAFE OPERATING AREA

